

# MDM1200H45E2

## FEATURES

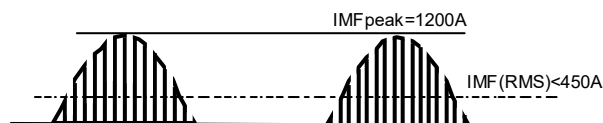
- \* Low VF diode module.
- \* Low noise recovery: Ultra soft fast recovery diode.
- \* High reverse recovery capability:  
Super HiRC Structure.
- \* High reliability, high durability diodes.
- \* Isolated heat sink (terminal to base).

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C )

Item	Symbol	Unit	MDM1200H45E2
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	V	4,500
Forward Current	AC peak	A	1,200
	1ms		I <sub>Fpulse</sub>
Operating Junction Temperature	T <sub>vj op</sub>	°C	-40 ~ +125
Storage Temperature	T <sub>stg</sub>	°C	-50 ~ +125 (1)
Isolation Test Voltage	Terminals-base	V <sub>ISO</sub>	10,200(AC 1 minute)
	Terminal 1-Terminal 2	V <sub>ISO T-T</sub>	10,200(AC 1 minute)
Screw Torque	Terminals (M8)	-	10 (2)
	Mounting (M6)	-	6 (3)

Notes: (1) Terminal temperature shall not exceed the specified temperature in any operation.

(2) Recommended Value 9±1N·m (3) Recommended Value 5.5±0.5N·m



## ELECTRICAL CHARACTERISTICS

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Repetitive Reverse Current	I <sub>RRM</sub>	mA	-	2.0	25	V <sub>R</sub> =4,500V, T <sub>vj</sub> =125°C
Forward Voltage Drop	V <sub>F</sub>	V	-	3.4	3.9	I <sub>F</sub> =1,200A, T <sub>vj</sub> =125°C
Reverse Recovery Time	t <sub>rr</sub>	μs	-	0.9	1.8	V <sub>CC</sub> =2,600V, I <sub>F</sub> =1,200A, L <sub>S</sub> =180nH
Reverse Recovery Loss	E <sub>rr(10%)</sub>	J/P	-	3.4	5.1	T <sub>vj</sub> =125°C, R <sub>G(on)</sub> =3.3Ω (4)
Partial discharge extinction voltage	V <sub>e</sub>	V <sub>RMS</sub>	3,500	-	-	f=50Hz, Q <sub>PD</sub> ≤10pC(acc. to IEC 61287)

Notes: (4) Counter arm; MBN1200H45E2 V<sub>GE</sub>=+/-15V

R<sub>G</sub> value is the test condition's value for evaluation of the switching times, not recommended value.

Please, determine the suitable R<sub>G</sub> value after the measurement of switching waveforms (overshoot voltage, etc.) with appliance mounted

## PACKAGE CHARACTERISTICS

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Terminal Resistance	R <sub>Ce</sub>	mΩ	-	0.3	-	per arm, T <sub>vj</sub> =25°C
Stray inductance module	L <sub>SCE</sub>	nH	-	42	-	per arm
Thermal Impedance	R <sub>th(j-c)</sub>	K/W	-	-	0.017	Junction to case (per arm)
Comparative tracking index	CTI		-	600	-	
Contact Thermal Impedance	R <sub>th(c-f)</sub>	K/W	-	0.007	-	Case to fin(λgrease=1W/(m·K), heat-sink flatness ≤50um)

\* Please contact our representatives at order.

\* For improvement, specifications are subject to change without notice.

\* For actual application, please confirm this spec sheet is the newest revision.

# MDM1200H45E2

## DEFINITION OF TEST CIRCUIT

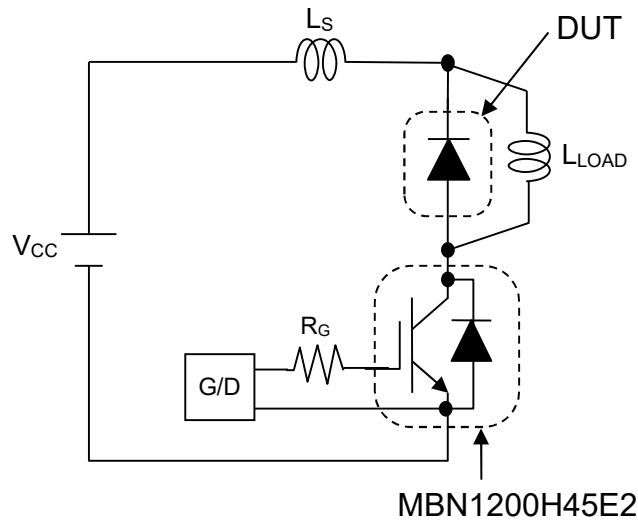


Fig.1 Switching test circuit

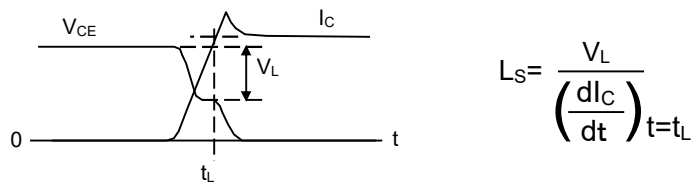
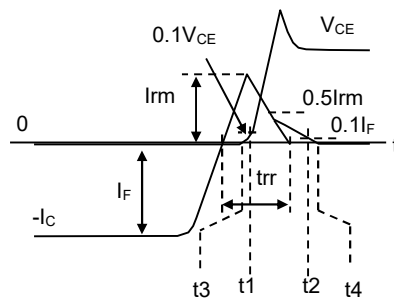


Fig.2 Definition of stray inductance



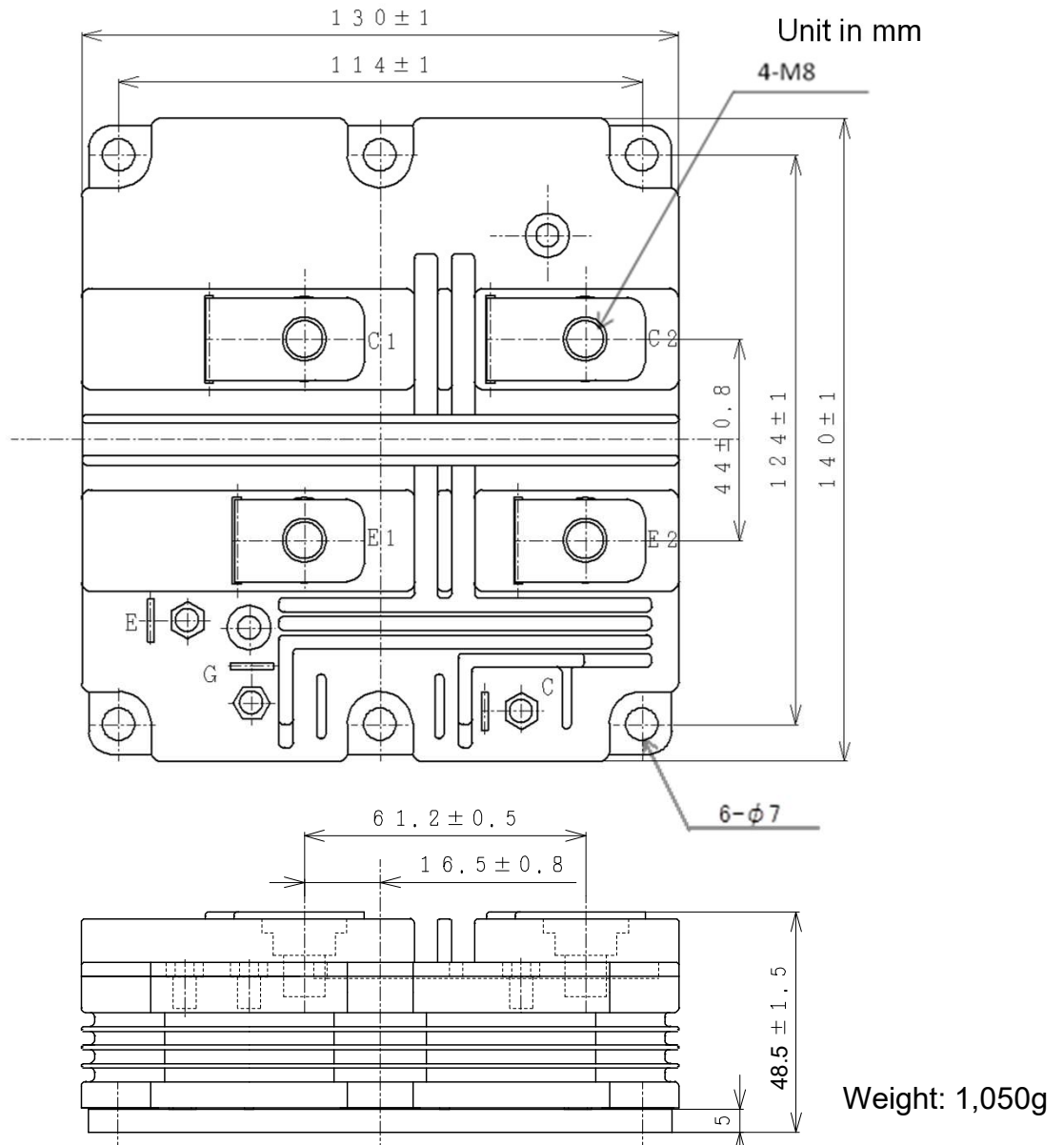
$$E_{rr(10\%)} = \int_{t_1}^{t_2} I_F \cdot V_{CE} dt$$

$$E_{rr(full)} = \int_{t_3}^{t_4} I_F \cdot V_{CE} dt$$

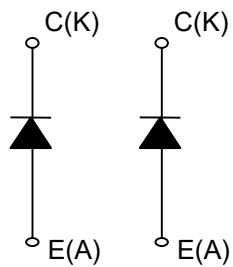
Fig.3 Definition of switching loss

# MDM1200H45E2

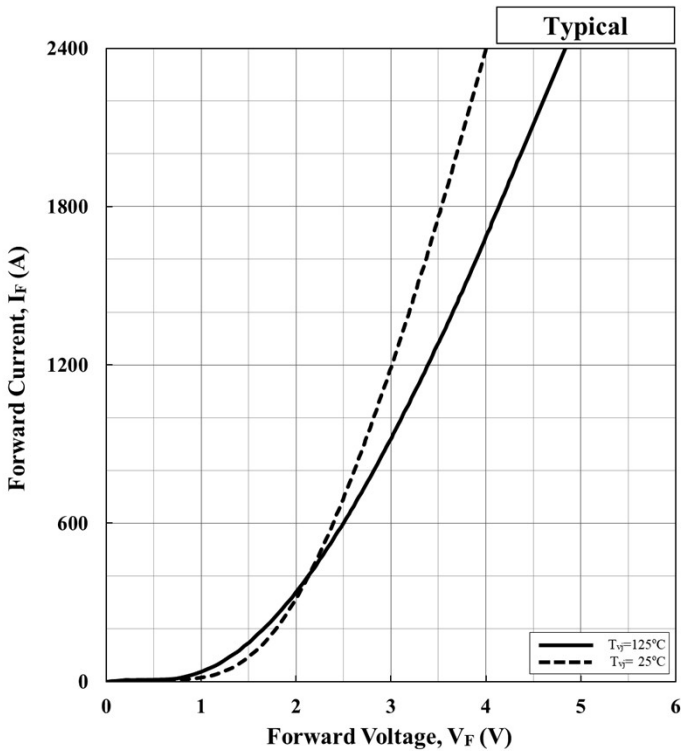
## OUTLINE DRAWING



## CIRCUIT DIAGRAM



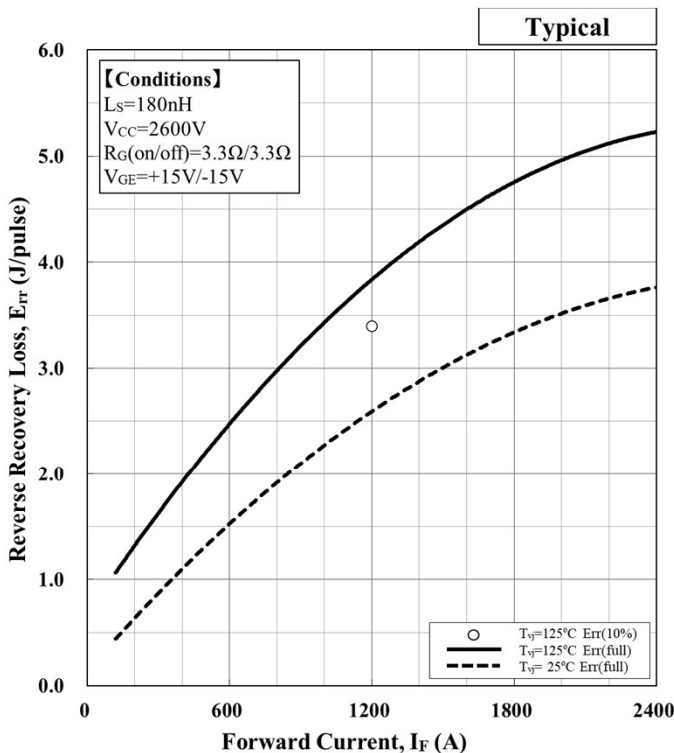
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$$V_F[V] = a_3 \cdot |I_F|^3 + a_2 \cdot |I_F|^2 + a_1 \cdot |I_F| + a_0$$

Temp.[°C]	$a_3$	$a_2$	$a_1$	$a_0$
25	1.34.E-10	-6.74.E-07	1.94.E-03	1.43.E+00
125	1.70.E-10	-8.72.E-07	2.66.E-03	1.17.E+00

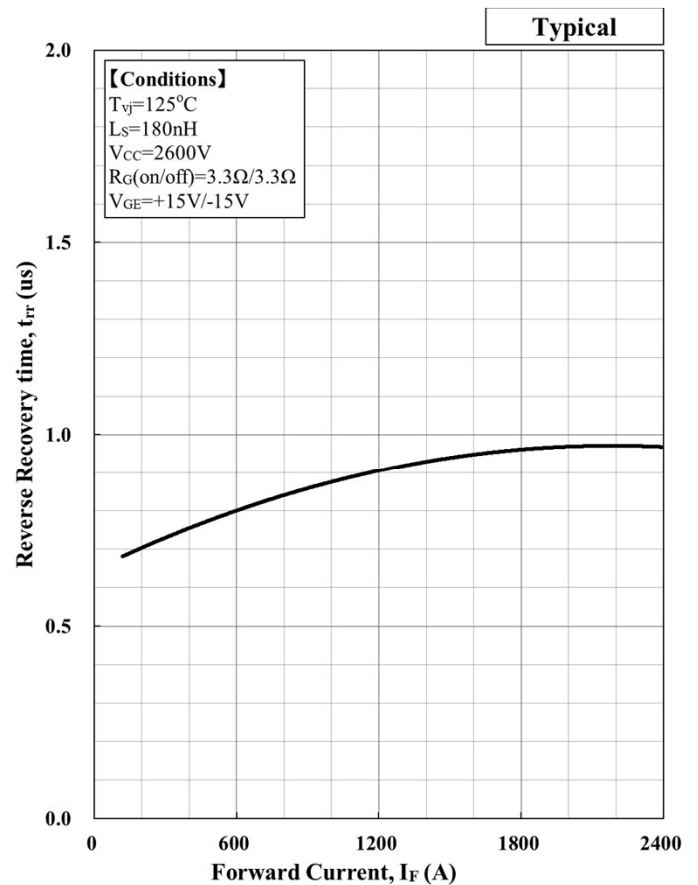
Forward Current vs. Forward Voltage



$$E [J] = a_3 \cdot |I_F|^3 + a_2 \cdot |I_F|^2 + a_1 \cdot |I_F| + a_0$$

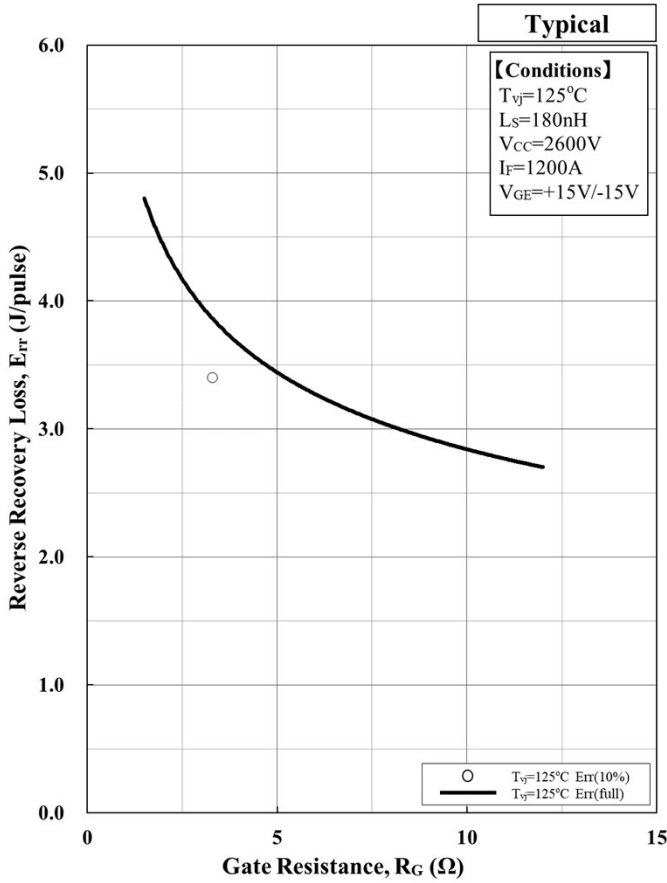
Temp.[°C]	$a_3$	$a_2$	$a_1$	$a_0$
25	-	-4.46E-07	2.58E-03	1.37E-01
125	-	-6.17E-07	3.38E-03	6.68E-01

Recovery loss vs. Forward current

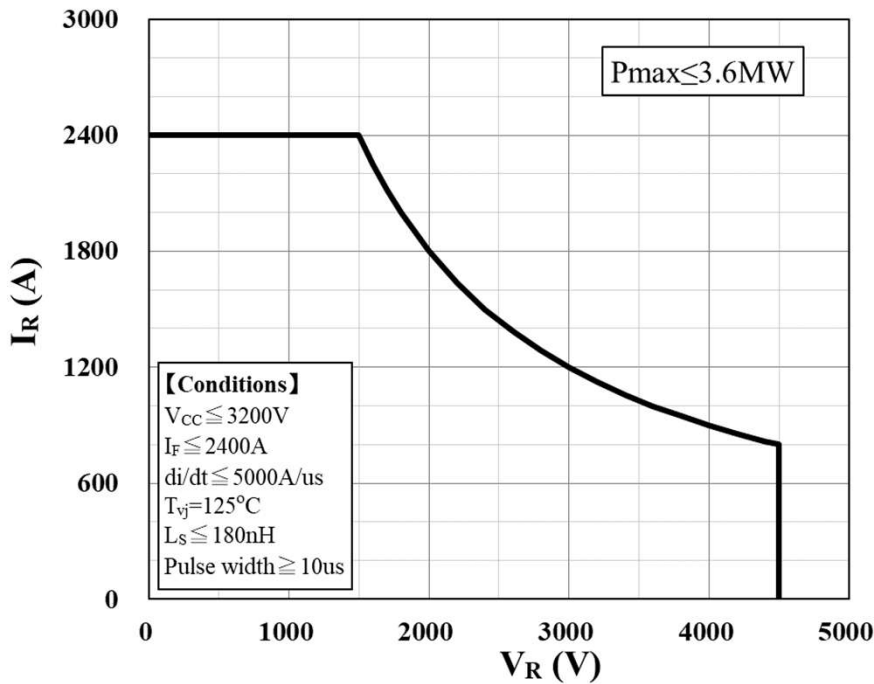


Reverse Recovery time vs. Forward Current

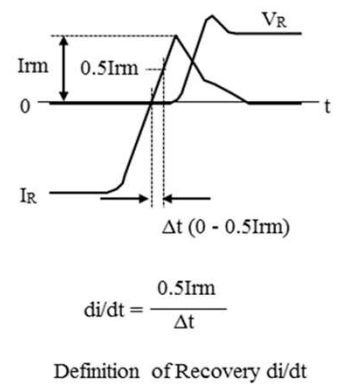
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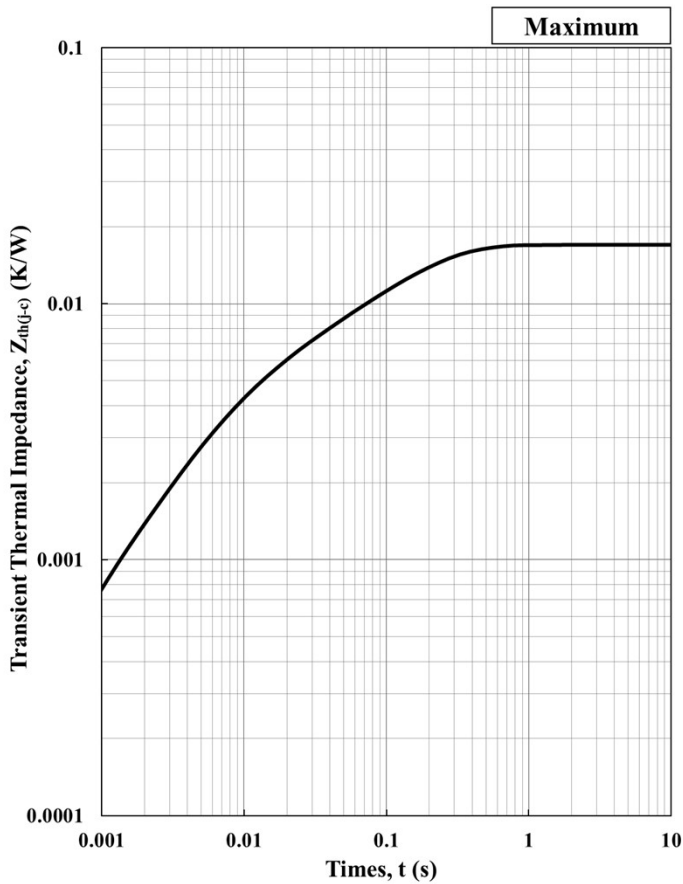
Reverse Recovery loss vs. Gate Resistance



(Defined at power terminal)  
Reverse Recovery Safe Operation Area ( RRSOA )



# MDM1200H45E2



**Transient Thermal Impedance Curve**

Foster model lumped circuit constant

n	1	2	3	4	Unit
R th, Diode [n]	1.05E-02	3.18E-03	3.14E-03	1.71E-04	[K/W]
C th, Diode [n]	1.55E+01	8.52E+00	1.95E+00	5.06E+00	[J/K]

Cauer model lumped circuit constant

n	1	2	3	4	Unit
R th, Diode [n]	2.51E-03	3.39E-03	5.27E-03	5.82E-03	[K/W]
C th, Diode [n]	1.12E+00	7.64E-01	6.19E+00	1.69E+01	[J/K]

**Material declaration**

Please note the following materials are contained in the product, in order to keep characteristic and reliability level.

Material	Contained part
Lead (Pb) and its compounds	Solder

# MDM1200H45E2

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5. A semi-processed article is done now using solder which contains lead inside the semiconductor devices. There is possibility of the regulation substance depend on the applied models, so please check before using.
6. This specification is a material for component selection, which describes specifications of power semiconductor devices (hereinafter referred to as products), characteristic charts, and external dimension drawings.
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8. For handling other than described in this manual, follow the handling instructions (IGBT-HI-00002).

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# MDM1200H45E2

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